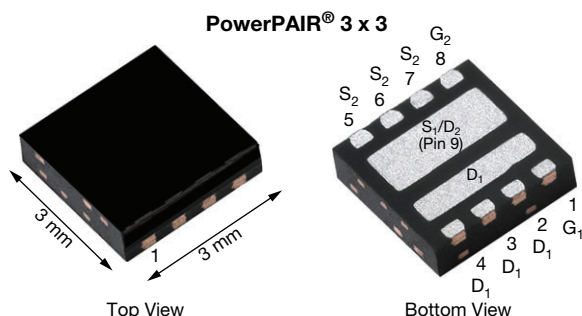


Dual N-Channel 30 V (D-S) MOSFET



FEATURES

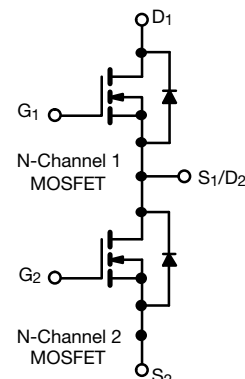
- TrenchFET® Gen IV power MOSFET
- High side and low side MOSFETs form optimized combination for 50 % duty cycle
- Optimized $R_{DS(on)}$ - Q_g and $R_{DS(on)}$ - Q_{gd} FOM elevates efficiency for high frequency switching
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Synchronous buck
- DC/DC conversion
- Half bridge
- POL



PRODUCT SUMMARY	
MOSFET CHANNEL-1 AND CHANNEL-2	
V_{DS} (V)	30
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10$ V	0.0094
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5$ V	0.0144
Q_g typ. (nC)	3.7
I_D (A)	33.4 ^a
Configuration	Dual

ORDERING INFORMATION	
Package	PowerPAIR 3 x 3
Lead (Pb)-free and halogen-free	SiZ342ADT-T1-GE3

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)				
PARAMETER		CHANNEL-1 AND CHANNEL-2		
		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	30	V
Gate-source voltage		V_{GS}	+20 / -16	
Continuous drain current ($T_J = 150$ °C)	$T_C = 25$ °C	I_D	33.4	A
	$T_C = 70$ °C		26.7	
	$T_A = 25$ °C		15.7 ^{b, c}	
	$T_A = 70$ °C		12.5 ^{b, c}	
Pulsed drain current ($t = 100$ μ s)		I_{DM}	100	
Continuous source current (MOSFET diode conduction)	$T_C = 25$ °C	I_S	13.9	
	$T_A = 25$ °C		3.1 ^{b, c}	
Single pulse avalanche current		I_{AS}	10	mJ
Single pulse avalanche energy		E_{AS}	5	
Maximum power dissipation	$T_C = 25$ °C	P_D	16.7	W
	$T_C = 70$ °C		10.7	
	$T_A = 25$ °C		3.7 ^{b, c}	
	$T_A = 70$ °C		2.4 ^{b, c}	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +150	°C
Soldering recommendations (peak temperature)			260	

Notes

- a. $T_C = 25$ °C
b. Surface mounted on 1" x 1" FR4 board
c. $t = 10$ s

**THERMAL RESISTANCE RATINGS**

PARAMETER		CHANNEL-1 AND CHANNEL-2			
		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^{a, b}	$t \leq 10$ s	R_{thJA}	27	34	°C/W
Maximum junction-to-case (drain)	Steady state	R_{thJC}	6	7.5	

Notes

a. Surface mounted on 1" x 1" FR4 board

b. Maximum under steady state conditions is 69 °C/W

SPECIFICATIONS ($T_J = 25$ °C, unless otherwise noted)

PARAMETER	CHANNEL-1 AND CHANNEL-2					
	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0$ V, $I_D = 250$ μ A	30	-	-	V
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250$ μ A	1	-	2.4	
Gate-source leakage	I_{GSS}	$V_{DS} = 0$ V, $V_{GS} = +20$ V / -16 V	-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 30$ V, $V_{GS} = 0$ V	-	-	1	μ A
		$V_{DS} = 30$ V, $V_{GS} = 0$ V, $T_J = 55$ °C	-	-	5	
On-state drain current ^a	$I_{D(on)}$	$V_{DS} \geq 5$ V, $V_{GS} = 10$ V	30	-	-	A
Drain-source on-state resistance ^a	$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 10$ A	-	0.0078	0.0094	Ω
		$V_{GS} = 4.5$ V, $I_D = 7$ A	-	0.0120	0.0144	
Forward transconductance ^a	g_{fs}	$V_{DS} = 10$ V, $I_D = 10$ A	-	57	-	S
Dynamic ^b						
Input capacitance	C_{iss}	$V_{DS} = 15$ V, $V_{GS} = 0$ V, $f = 1$ MHz	-	580	-	pF
Output capacitance	C_{oss}		-	250	-	
Reverse transfer capacitance	C_{rss}		-	30	-	
C_{rss}/C_{iss} ratio			-	0.052	0.103	
Total gate charge	Q_g	$V_{DS} = 15$ V, $V_{GS} = 10$ V, $I_D = 15.7$ A	-	8.1	12.2	nC
Gate-source charge	Q_{gs}	$V_{DS} = 15$ V, $V_{GS} = 4.5$ V, $I_D = 15.7$ A	-	3.7	4.5	
Gate-drain charge	Q_{gd}		-	2.4	-	
Gate resistance	R_g		-	0.67	-	
Turn-on delay time	$t_{d(on)}$	$f = 1$ MHz	0.24	1.2	2.4	Ω
Rise time	t_r		-	10	20	ns
Turn-off delay time	$t_{d(off)}$		-	10	20	
Fall time	t_f		-	6	12	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 15$ V, $R_L = 1.2$ Ω , $I_D \cong 12.5$ A, $V_{GEN} = 10$ V, $R_g = 1$ Ω	-	18	36	
Rise time	t_r		-	8	16	
Turn-off delay time	$t_{d(off)}$		-	15	30	
Fall time	t_f		-	180	360	
		$V_{DD} = 15$ V, $R_L = 1.2$ Ω , $I_D \cong 12.5$ A, $V_{GEN} = 4.5$ V, $R_g = 1$ Ω	-	20	40	
			-	15	30	

**SPECIFICATIONS** ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

PARAMETER	CHANNEL-1 AND CHANNEL-2					
	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain-source Body Diode Characteristics						
Continuous source-drain diode current	I_S	$T_C = 25^{\circ}\text{C}$	-	-	13.9	A
Pulse diode forward current	I_{SM}		-	-	100	
Body diode voltage	V_{SD}	$I_S = 12.5\text{ A}$, $V_{GS} = 0\text{ V}$	-	0.85	1.2	V
Body diode reverse recovery time	t_{rr}	$I_F = 12.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^{\circ}\text{C}$	-	15	30	ns
Body diode reverse recovery charge	Q_{rr}		-	4.3	8.6	nC
Reverse recovery fall time	t_a		-	8	-	ns
Reverse recovery rise time	t_b		-	7	-	

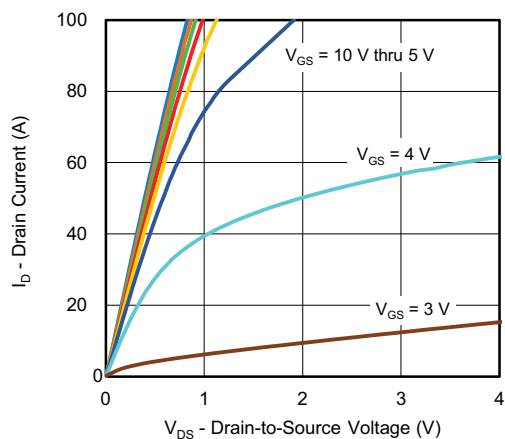
Notes

- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
- Guaranteed by design, not subject to production testing

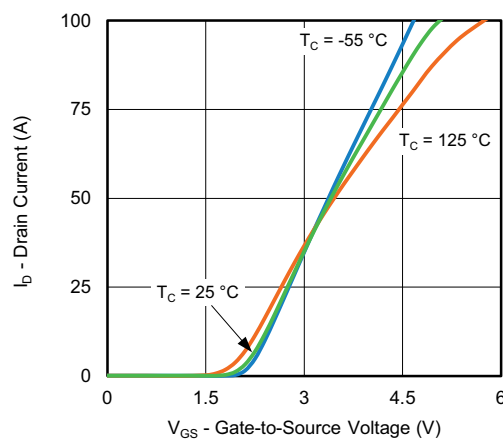
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



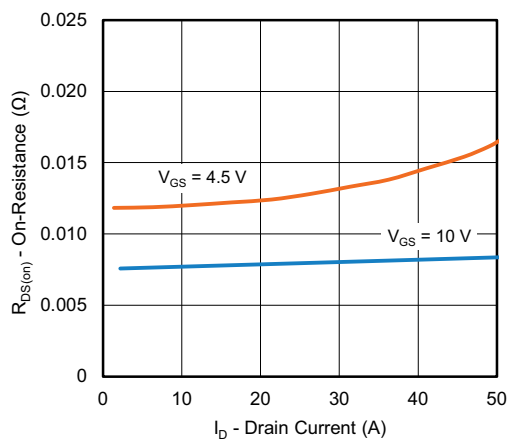
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



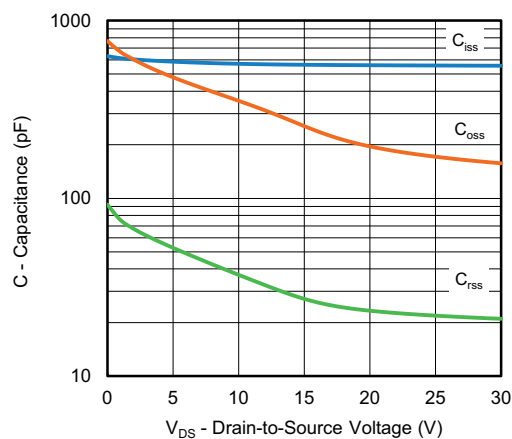
Output Characteristics



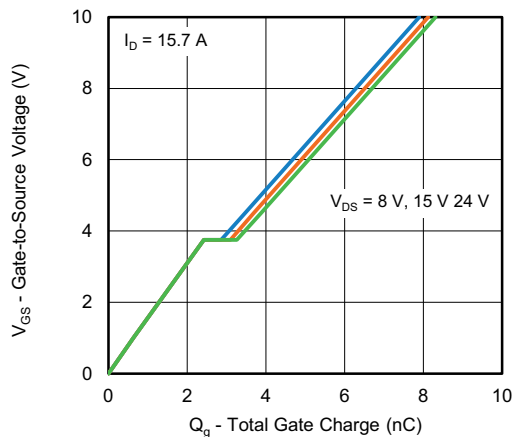
Transfer Characteristics



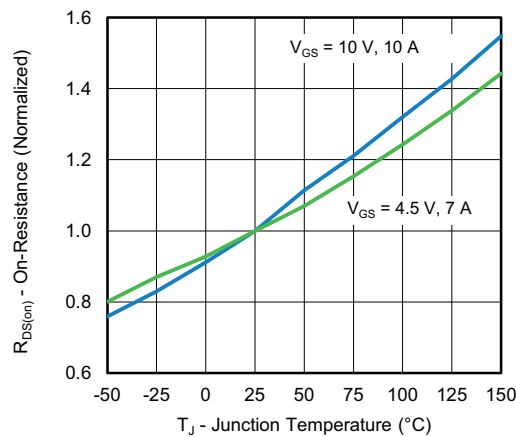
On-Resistance vs. Drain Current and Gate



Capacitance



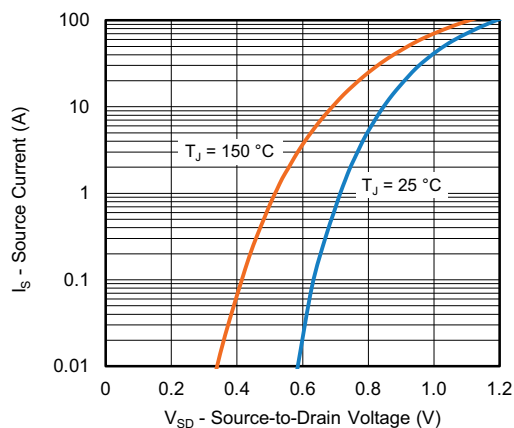
Gate Charge



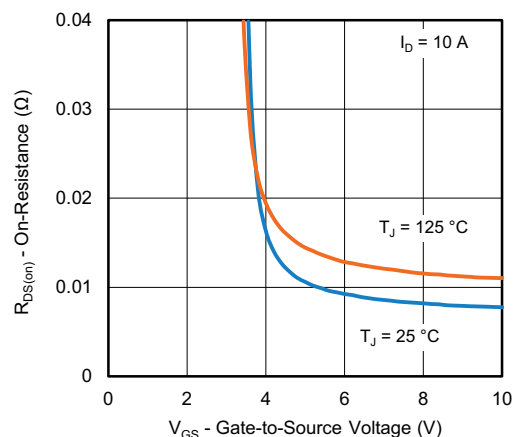
On-Resistance vs. Junction Temperature



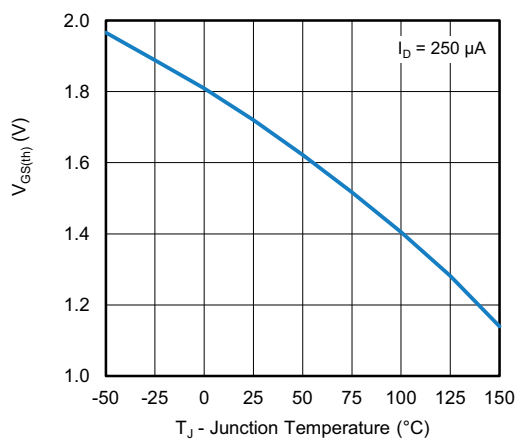
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



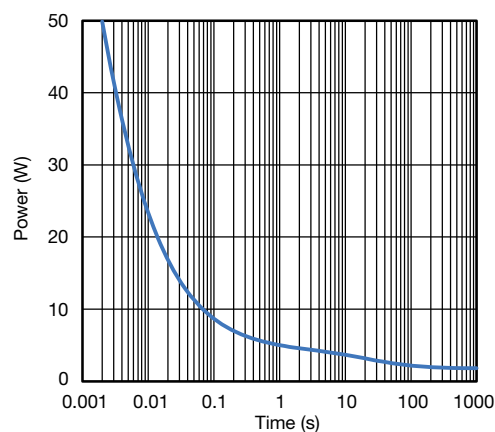
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



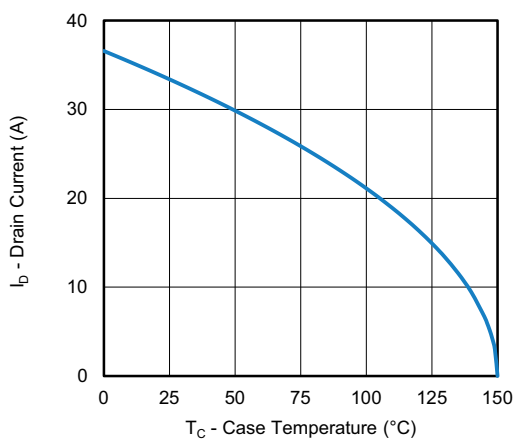
Threshold Voltage



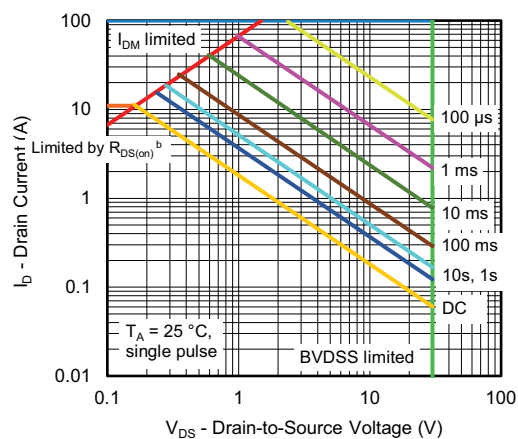
Single Pulse Power



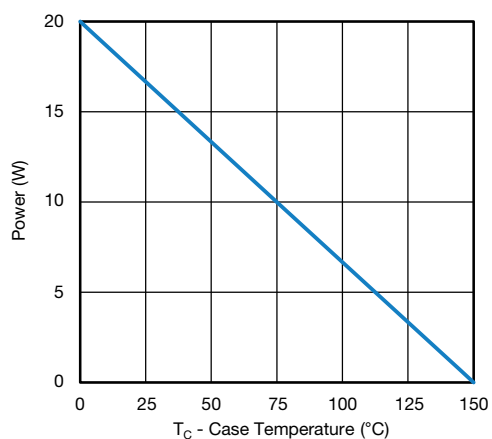
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



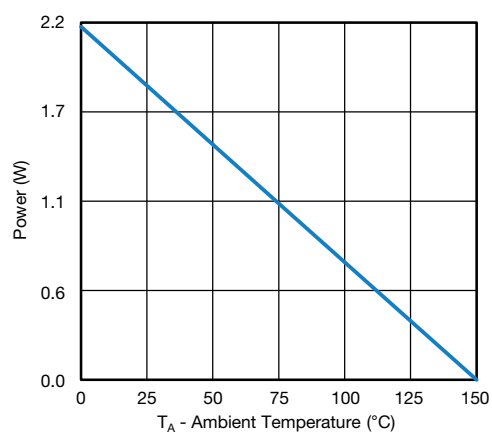
Current Derating ^a



Safe Operating Area, Junction-to-Ambient



Power, Junction-to-Case



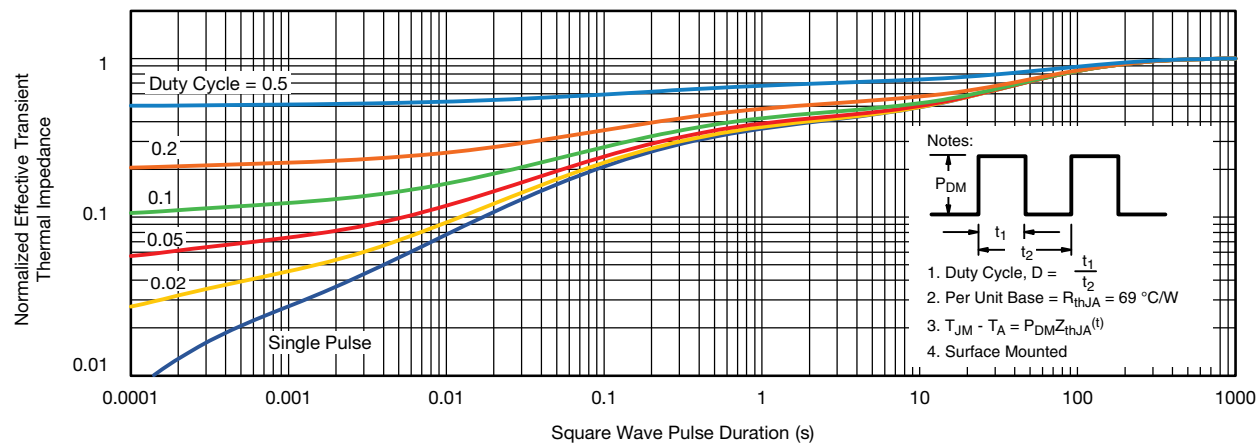
Power, Junction-to-Ambient

Notes

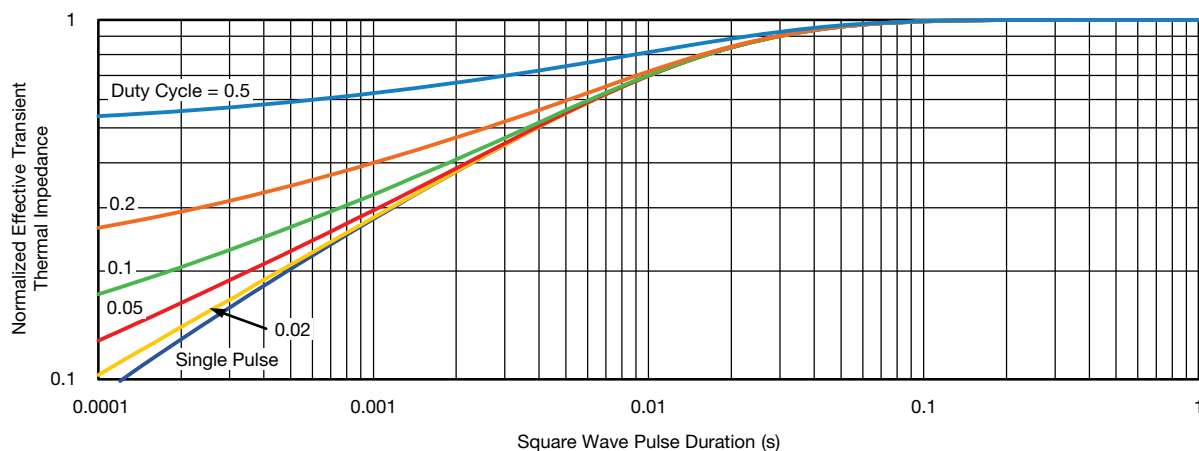
- The power dissipation P_D is based on $T_J \text{ max.} = 150^\circ\text{C}$, using junction-to-ambient thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit
- $V_{GS} > \text{minimum } V_{GS}$ at which $R_{DS(on)}$ is specified



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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